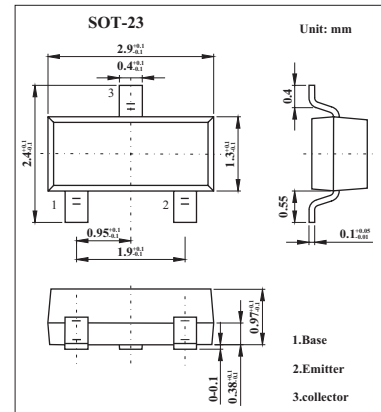


Silicon NPN Epitaxial

2SC2619

■ Features

- High frequency amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	100	mA
Collector dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA , I _E = 0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA , R _{BE} = ∞	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _C = 0	5			V
Collector cutoff current	I _{CBO}	V _{CB} = 20V , I _E =0			0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 2V , I _C =0			0.5	μA
DC current gain	h _{FE}	V _{CE} = 12V , I _C = 2mA	60		200	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 10mA , I _B = 1mA			1.1	V
Base-emitter voltage	V _{BE}	V _{CE} = 12V , I _C = 2mA			0.75	V
Gain bandwidth product	f _T	V _{CE} = 12V , I _C = 2mA		230		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V , I _E =0, f = 1MHz			3.5	pF
Noise figure	NF	V _{CE} = 6V , I _C = 2mA, f = 1MHz, R _g = 500Ω		5		dB

■ hFE Classification

Marking	FB	FC
hFE	60~120	100~200